## Introduction to CMOS VLSI Design

# Lecture 8: Combinational Circuits 

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## Outline

- Bubble Pushing
- Compound Gates
- Logical Effort Example
- Input Ordering
- Asymmetric Gates
- Skewed Gates
- Best P/N ratio


## Example 1

```
module mux(input s, d0, d1,
    output y);
    assign y = s ? d1 : d0;
endmodule
```

1) Sketch a design using AND, OR, and NOT gates.

## Example 2

2) Sketch a design using NAND, NOR, and NOT gates. Assume ~S is available.

## Example 3

3) Sketch a design using one compound gate and one NOT gate. Assume ~S is available.

## Compound Gates

- Logical Effort of compound gates
unit inverter
$Y=\bar{A}$


$g_{A}=3 / 3$
$p=3 / 3$
$Y=\frac{\mathrm{AOL21}}{A \cdot B+C}$
$Y=\frac{\text { AOI22 }}{A \cdot B+C \cdot D}$


$g_{A}=$
$g_{A}=$
$g_{B}=$
$g_{c}=$
$g_{D}=$
$\mathrm{g}_{\mathrm{E}}=$
$\mathrm{p}=$


## Example 4

- The multiplexer has a maximum input capacitance of 16 units on each input. It must drive a load of 160 units. Estimate the delay of the NAND and compound gate designs.


## NAND Solution



## Compound Solution



## Example 5

- Annotate your designs with transistor sizes that achieve this delay.



## Input Order

- Our parasitic delay model was too simple
- Calculate parasitic delay for Y falling
- If A arrives latest?
- If B arrives latest?



## Inner \& Outer Inputs

- Outer input is closest to rail (B)
- Inner input is closest to output (A)
- If input arrival time is known
- Connect latest input to inner terminal


## Asymmetric Gates

- Asymmetric gates favor one input over another
[ Ex: suppose input A of a NAND gate is most critical
- Use smaller transistor on A (less capacitance)
- Boost size of noncritical input
- So total resistance is same
- $g_{A}=$
- $g_{B}=$
- $g_{\text {total }}=g_{A}+g_{B}=$


I Asymmetric gate approaches $\mathrm{g}=1$ on critical input

- But total logical effort goes up


## Symmetric Gates

$\square$ Inputs can be made perfectly symmetric


## Skewed Gates

- Skewed gates favor one edge over another
$\square$ Ex: suppose rising output of inverter is most critical
- Downsize noncritical nMOS transistor

unskewed inverter unskewed inverter (equal rise resistance) (equal fall resistance)


- Calculate logical effort by comparing to unskewed inverter with same effective resistance on that edge.
$-g_{u}=$
$-g_{d}=$


## HI- and LO-Skew

- Def: Logical effort of a skewed gate for a particular transition is the ratio of the input capacitance of that gate to the input capacitance of an unskewed inverter delivering the same output current for the same transition.
- Skewed gates reduce size of noncritical transistors
- HI-skew gates favor rising output (small nMOS)
- LO-skew gates favor falling output (small pMOS)
- Logical effort is smaller for favored direction
- But larger for the other direction


# Catalog of Skewed Gates 



Inverter
unskewed




NAND2
NOR2




## Asymmetric Skew

- Combine asymmetric and skewed gates
- Downsize noncritical transistor on unimportant input
- Reduces parasitic delay for critical input



## Best P/N Ratio

- We have selected $\mathrm{P} / \mathrm{N}$ ratio for unit rise and fall resistance ( $\mu=2-3$ for an inverter).
] Alternative: choose ratio for least average delay
[ Ex: inverter
- Delay driving identical inverter
$-t_{\text {pdf }}=$
$-t_{\mathrm{pdr}}=$
$-t_{p d}=$
- Differentiate $\mathrm{t}_{\mathrm{pd}}$ w.r.t. P
- Least delay for $\mathrm{P}=$


## P/N Ratios

- In general, best $\mathrm{P} / \mathrm{N}$ ratio is sqrt of equal delay ratio.
- Only improves average delay slightly for inverters
- But significantly decreases area and power


NAND2


NOR2


## Observations

- For speed:
- NAND vs. NOR
- Many simple stages vs. fewer high fan-in stages
- Latest-arriving input
$\square$ For area and power:
- Many simple stages vs. fewer high fan-in stages

